NTMFS6D1N08HT1G Datasheet

DiGi Electronics Part Number	NTMFS6D1N08HT1G-DG
Manufacturer	onsemi
Manufacturer Product Number	NTMFS6D1N08HT1G
Description	MOSFET N-CH 80V 17A/89A 5DFN
Detailed Description	N-Channel 80 V 17A (Ta), 89A (Tc) 3.8W (Ta), 104W (Tc) Surface Mount 5-DFN (5x6) (8-SOFL)

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
NTMFS6D1N08HT1G	onsemi
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
80 V	17A (Ta), 89A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
6V, 10V	5.5mOhm @ 20A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 120µA	32 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	2085 pF @ 40 V
FET Feature:	Power Dissipation (Max):
-	3.8W (Ta), 104W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 175°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
5-DFN (5x6) (8-SOFL)	8-PowerTDFN, 5 Leads
Base Product Number:	
NTMFS6	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

onsemi

DATA SHEET
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MOSFET – Power, Single, N-Channel

80 V, 5.5 mΩ, 89 A

NTMFS6D1N08H

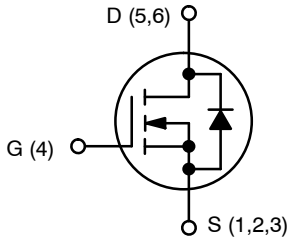
$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
80 V	5.5 mΩ @ 10 V	89 A
	8.0 mΩ @ 6 V	

Features

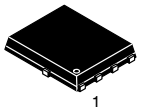
- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- These Devices are Pb−Free, Halogen Free/BFR Free, Beryllium Free and are RoHS Compliant

Typical Applications

- Synchronous Rectification
- AC−DC and DC−DC Power Supplies
- AC−DC Adapters (USB PD) SR
- Load Switch

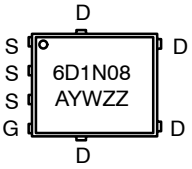


N−CHANNEL MOSFET



DFN5
(SO−8FL)
CASE 488AA
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	80	V
Gate−to−Source Voltage			V_{GS}	±20	V
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	T_C = 25°C	I_D	89	A
Power Dissipation $R_{\theta JC}$ (Note 1)			P_D	104	W
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	T_A = 25°C	I_D	17	A
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)			P_D	3.8	W
Pulsed Drain Current	T_A = 25°C, t_p = 10 μs		I_{DM}	468	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	87	A
Single Pulse Drain−to−Source Avalanche Energy (I_{AV} = 5.9 A)			E_{AS}	465	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8″ from case for 10 s)			T_L	300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case − Steady State (Note 1)	$R_{\theta JC}$	1.44	°C/W
Junction−to−Ambient − Steady State (Note 1)	$R_{\theta JA}$	40	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface−mounted on FR4 board using 1 in^2 pad size, 1 oz. Cu pad.

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS6D1N08HT1G	DFN5 (Pb−Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NTMFS6D1N08H

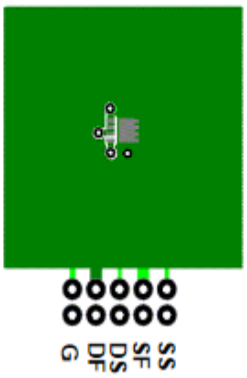
ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		80			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 250 μA, ref to 25°C			43.8		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 80 V	T_J = 25°C			10	μA
			T_J = 125°C			100	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V				100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 120 μA		2.0		4.0	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	I_D = 250 μA, ref to 25°C			−7.08		mV/°C
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A			4.5	5.5	mΩ
		V_{GS} = 6 V, I_D = 10 A			6.4	8.0	
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 20 A			80		S
Gate−Resistance	R_G	T_A = 25°C			1.0		Ω
CHARGES & CAPACITANCES							
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 40 V			2085		pF
Output Capacitance	C_{OSS}				300		
Reverse Transfer Capacitance	C_{RSS}				10		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 6 V, V_{DS} = 40 V, I_D = 30 A			10		nC
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 40 V, I_D = 30 A			32		nC
Gate−to−Source Charge	Q_{GS}				10		
Gate−to−Drain Charge	Q_{GD}				6		
Plateau Voltage	V_{GP}				5		V
SWITCHING CHARACTERISTICS (Note 3)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 64 V, I_D = 30 A, R_G = 2.5 Ω			18		ns
Rise Time	t_r				50		
Turn−Off Delay Time	$t_{d(OFF)}$				48		
Fall Time	t_f				39		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = 20 A	T_J = 25°C		0.8	1.2	V
			T_J = 125°C		0.7		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 20 A			49		ns
Reverse Recovery Charge	Q_{RR}				60		nC
Charge Time	t_a	V_{GS} = 0 V, dI_S/dt = 100 A/μs, I_S = 20 A			30		ns
Discharge Time	t_b				19		ns

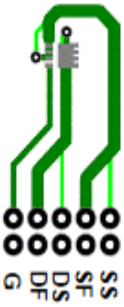
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures
4. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR−4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

NTMFS6D1N08H



a) 53°C/W when mounted on a 1 in^2 pad of 2 oz copper.



b) 125°C/W when mounted on a minimum pad of 2 oz copper.

5. Pulse Test: pulse width < 300 μs, duty cycle < 2%.
6. E_{AS} of 465 mJ is based on started T_J = 25°C, I_{AS} = 5.9 A, V_{DD} = 80 V, V_{GS} = 10 V. 100% test at I_{AS} = 8.4 A.
7. As an N−ch device, the negative Vgs rating is for low duty cycle pulse occurrence only. No continuous rating is implied.

NTMFS6D1N08H

TYPICAL CHARACTERISTICS

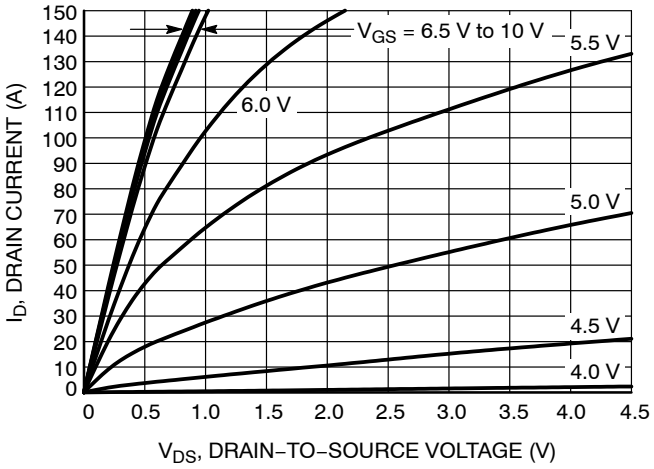


Figure 1. On−Region Characteristics

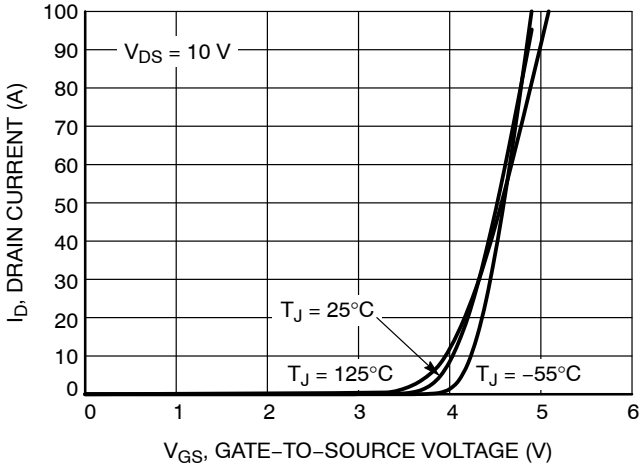


Figure 2. Transfer Characteristics

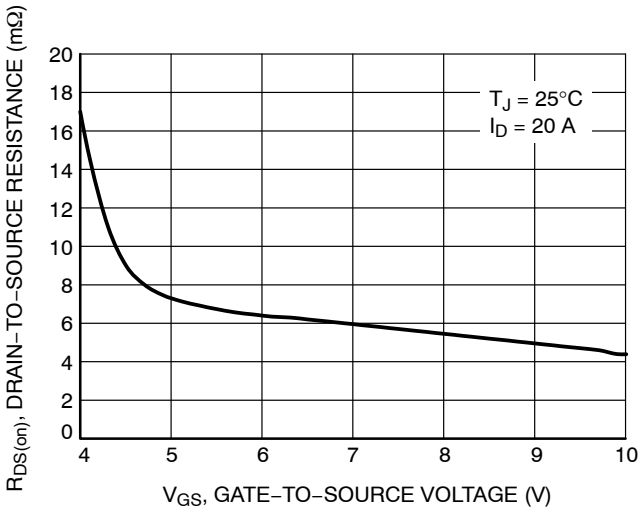


Figure 3. On−Resistance vs. Gate−to−Source Voltage

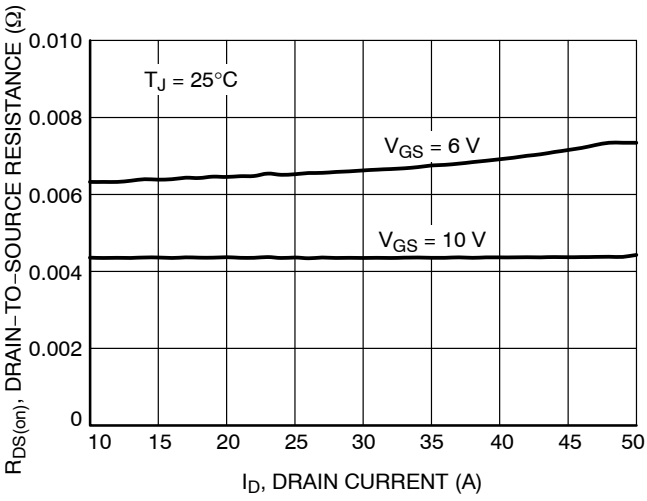


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

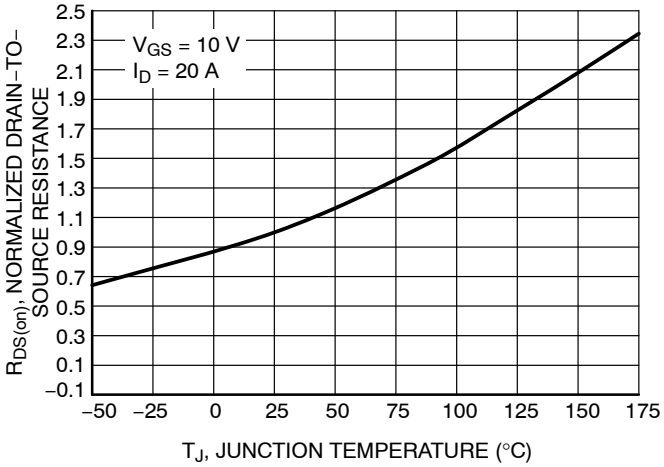


Figure 5. On−Resistance Variation with Temperature

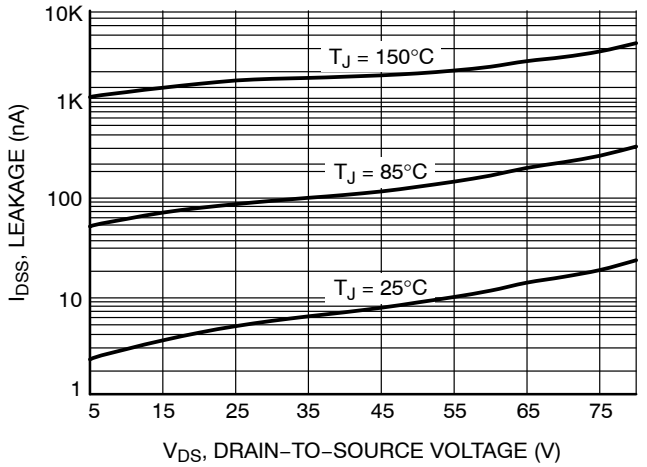


Figure 6. Drain−to−Source Leakage Current vs. Voltage

NTMFS6D1N08H

TYPICAL CHARACTERISTICS

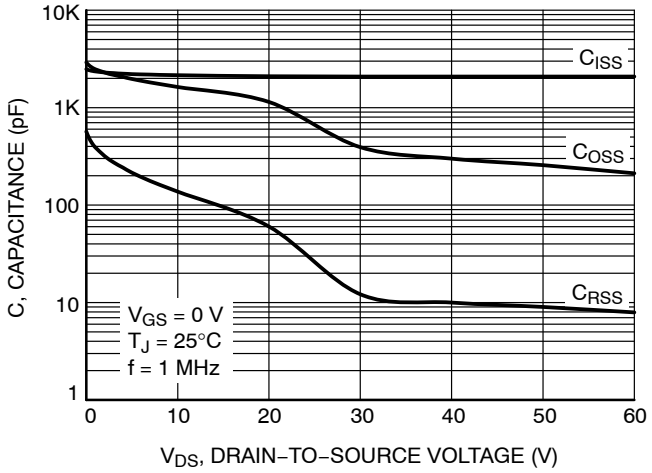


Figure 7. Capacitance Variation

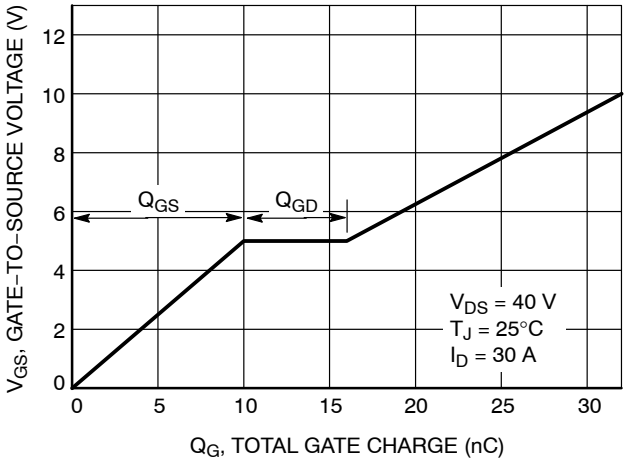


Figure 8. Gate−to−Source Voltage vs. Total Charge

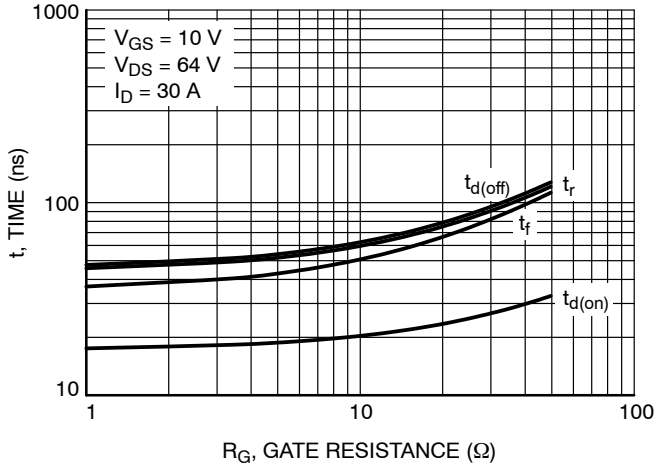


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

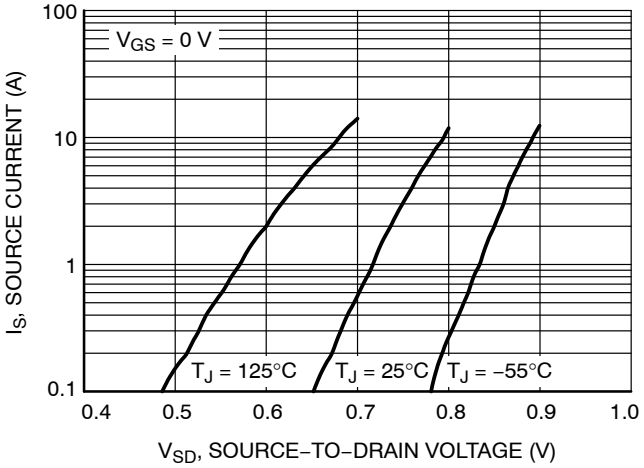


Figure 10. Diode Forward Voltage vs. Current

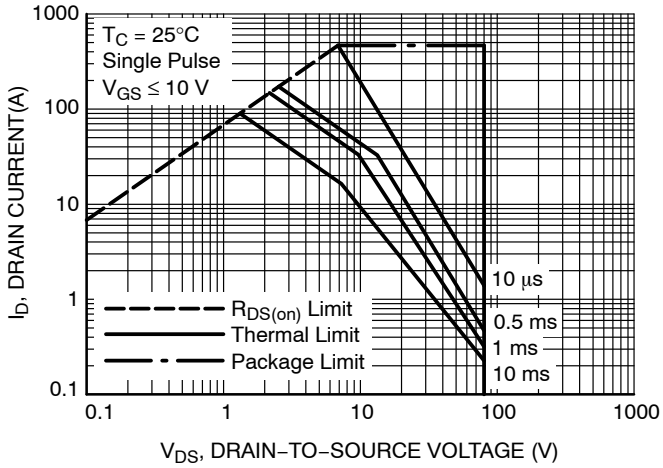


Figure 11. Maximum Rated Forward Biased Safe Operating Area

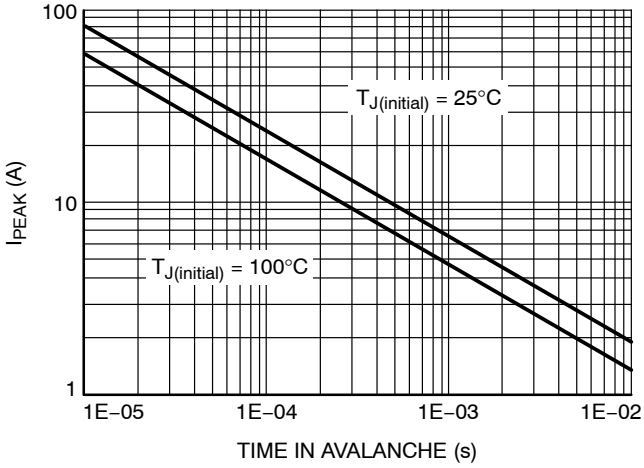


Figure 12. I_{PEAK} vs. Time in Avalanche

NTMFS6D1N08H

TYPICAL CHARACTERISTICS

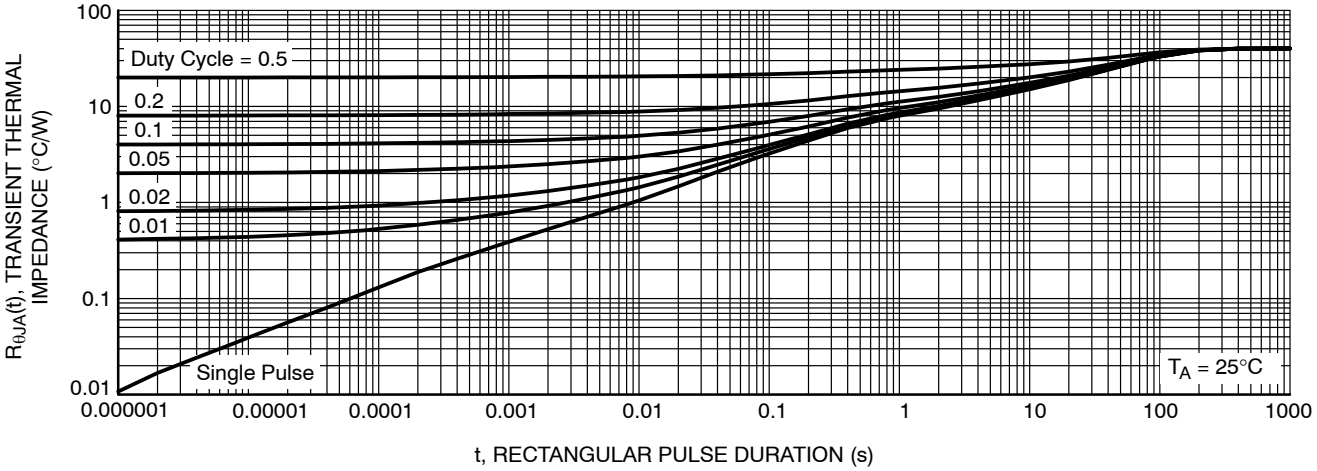


Figure 13. Thermal Response

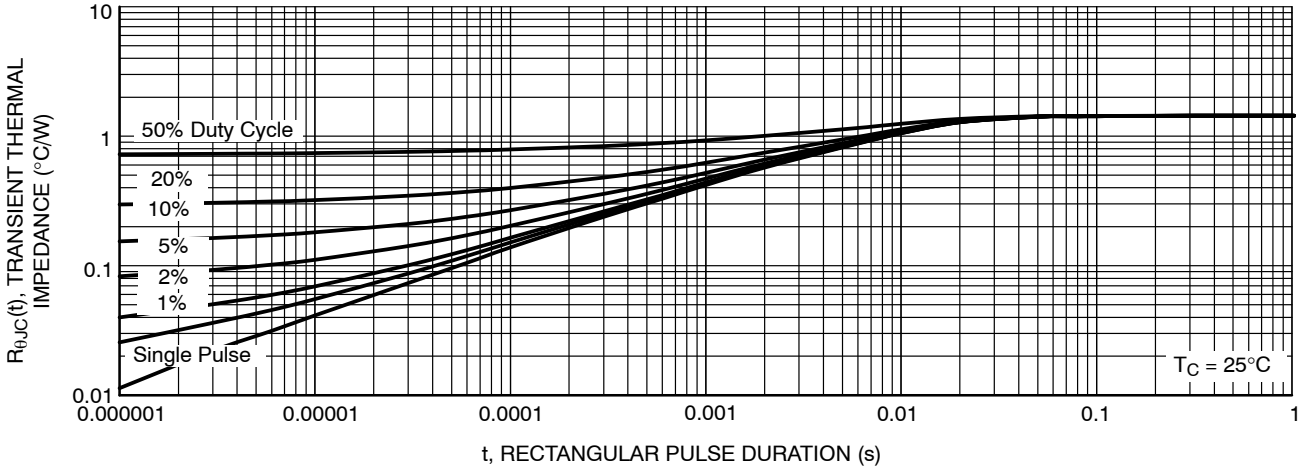
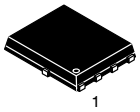


Figure 14. Thermal Response

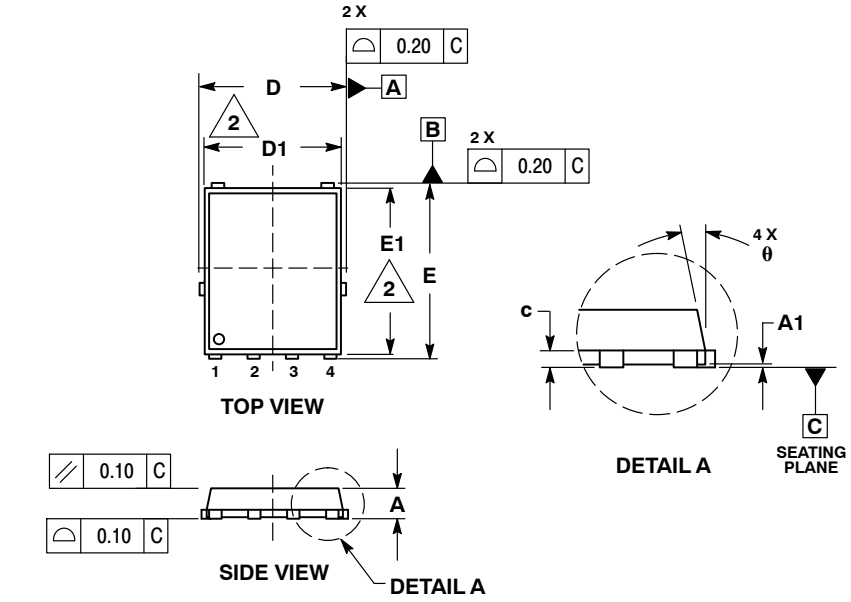
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SCALE 2:1

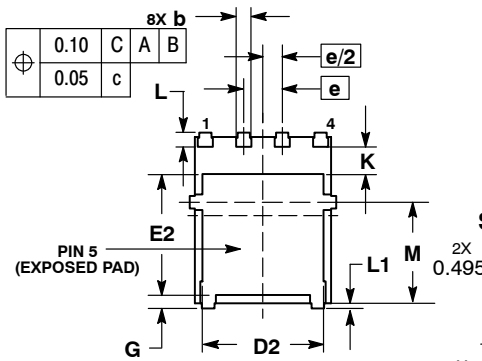
DFN5 5x6, 1.27P
(SO−8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

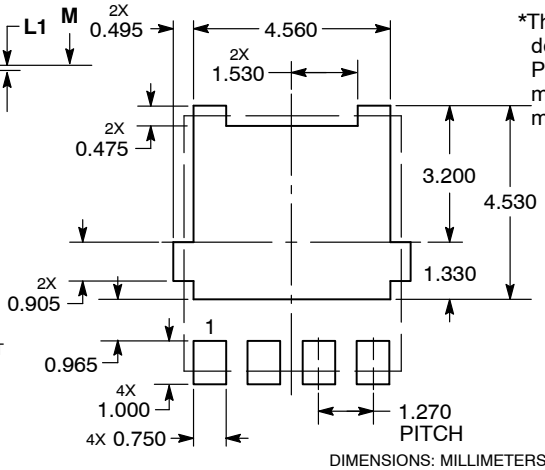
	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	–––	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	–––	12 °



STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

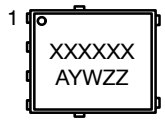
RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	**DFN5 5x6, 1.27P (SO−8FL)**		**PAGE 1 OF 1**

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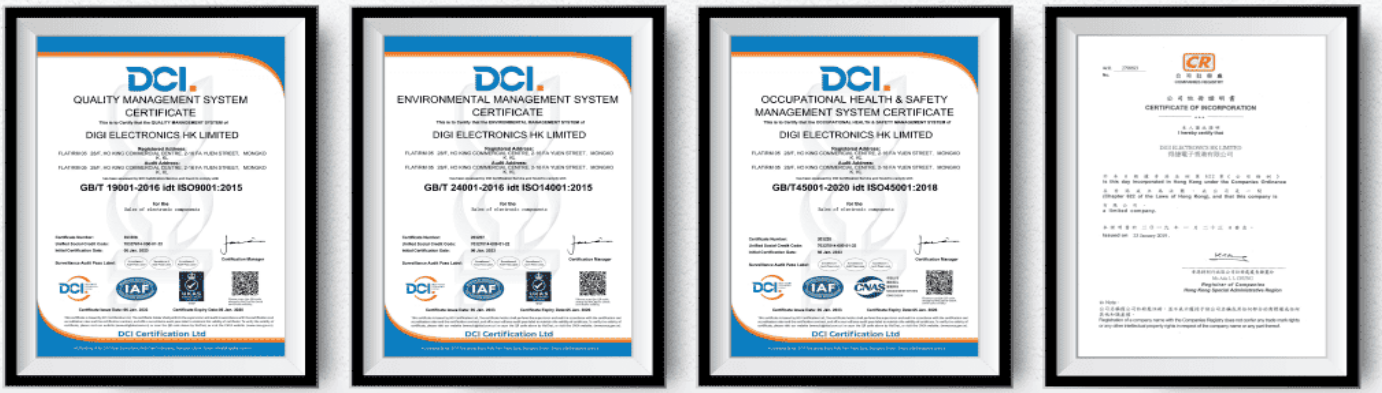

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